Signal Analysis

... (10.80

veen input and

50 kΩ. Calculate

5.1K S×50K E.D.C.-I

635

**FET Small Signal Analysis** 

iii)  $A_v$ : From equation 10.80 we have

$$A_{v} = \frac{R_{D}(1 + g_{m} r_{d})}{r_{d} + R_{D}} = \frac{5.1 \text{ K}(1 + 2.8 \text{ mS} \times 50 \text{ K})}{50 \text{ K} + 5.1 \text{ K}}$$
$$= 13.05$$

## 10.7 Depletion - Type MOSFET Amplifier

Fig. 10.30 shows as equivalent model of depletion type MOSFET.

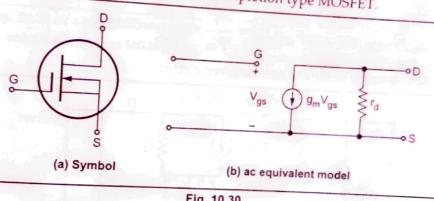


Fig. 10.30

This is exactly same as that of JFET. The only difference is that in depletion layer. MOSFET. V<sub>GSQ</sub> can be positive for n-channel MOSFET and negative for p-channel

Due to this in depletion MOSFET,  $g_m$  can be greater than  $g_{mo}$ . This is illustrated in the following example.

Ex. 10.7: For the circuit shown in Fig. 10.31  $V_{GSQ} = 2V$ , with  $I_{dQ} = 5$  mA and  $y_{os} = 20$  mS Calculate gm, rd, Zi, Zo and Av.

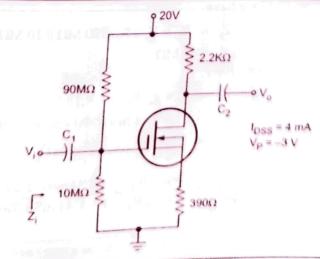


Fig. 10.31

636

E.D.C.-1

$$g_{mo} = \frac{2I_{dSS}}{|V_P|} = \frac{2(4 \text{ mA})}{3 \text{ V}} = 2.67 \text{ mS}$$

Solution:

 $g_m = g_{mo} \left(1 - \frac{V_{GSQ}}{V_P}\right) = 2.67 \text{ mS} \left(1 - \frac{2V}{-3 \text{ V}}\right)$ 
 $= 4.44 \text{ mS}$ 

We observed that,  $g_m$  is greater than  $g_{mo}$  if  $V_{GSQ}$  is positive in n-channel  $d_{ep}$ 

type MOSFET.

ii)

 $r_d = \frac{1}{v_{cs}} = \frac{1}{20 \,\mu\text{S}} = 50 \,\text{k}\Omega$ 

Fig. 10.32 shows the ac equivalent for given circuit.

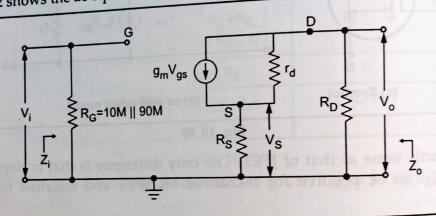


Fig. 10.32

This ac equivalent is exactly same as the circuit given in Fig. 10.18. The formulae applicable for ac equivalent circuit given in the Fig. 10.18 are also applicable the circuit given in Fig. 10.28 the circuit given in Fig. 10.32.

iii) Z<sub>i</sub>: From equation 10.42 we have

$$Z_i = R_G = R_1 || R_2 = 90 \text{ M}\Omega || 10 \text{ M}\Omega$$
  
= 9 M\Omega

iv)  $Z_0$ : From equation 10.45 we have,

$$Z_o = [1 + g_m R_s r_d + R_s] || R_D$$
  
= [1 + 4.44 mS × 390 × 50 K + 390] || 2.2 K  
= 2146 \Omega

v) A<sub>v</sub>: From equation 10.48 we have

$$A_{v} = \frac{-g_{m} R_{d}}{1 + g_{m} R_{s}} = \frac{-4.44 \text{ mS} \times 2.2 \text{ K}}{1 + 4.44 \text{ mS} \times 390}$$
$$= 3.576$$

E.D.C.-I

10.8 Enh

Thus, di follows,

10.8.1 Enh

Fig. 10.3

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## 10.8 Enhancement-Type MOSFET Amplifier

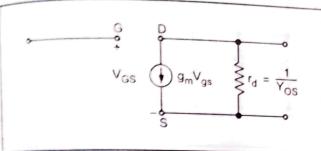


Fig. 10.33 ac equivalent model of enhancement type MOSFET

Fig. 10.33 shows ac equivalent model of enhancement type MOSFET. This is exactly same as that of JFET. The only difference is that in enhancement type MOSFET, V<sub>GSQ</sub> is positive for n channel MOSFET and negative for p-channel MOSFET.

We know that, in enhancement type MOSFET relationship between output current  $I_d$  and controlling voltage  $V_{GS}$  is given as,

$$I_d = K(V_{GS} - V_T)^2 \qquad \dots (10.82 \text{ a})$$
 where 
$$K = \frac{I_d (ON)}{(V_{GS}(ON) - V_T)^2}$$
 
$$g_m = \frac{\Delta I_D}{\Delta V_{GS}} \qquad \dots (10.82 \text{ b})$$

Thus, differentiating equation 10.82 with respect to  $V_{GS}$  we get the equation for  $g_m$  as follows.

$$g_{m} = \frac{I_{D}}{V_{GS}}$$

$$= V_{GS} [K (V_{GS} - V_{T})]^{2}$$

$$= 2K (V_{GS} - V_{T})$$
 ... (10.83)

## 19.8.1 Enhancement Type MOSFET with Feedback Bias

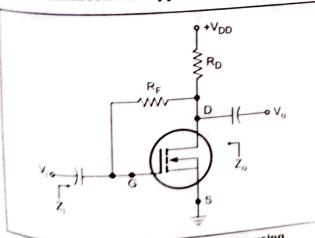


Fig. 10.34 Common source amplifier using enhancement type MOSFET

Fig. 10.34 shows common source amplifier using enhancement type MOSFET. In this circuit biasing is provided by feedback bias.

Replacing enhancement type MOSFET with its ac equivalent and capacitors and dc voltage source with short circuits, we get ac equivalent model shown in the Fig. 10.35.

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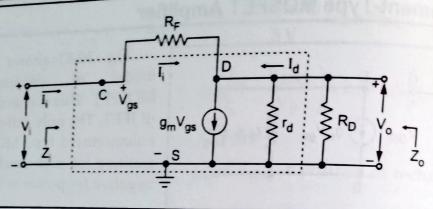


Fig. 10.35 ac equivalent circuit of circuit shows in Fig. 10.34

Input impedance Zi: It is given as,

$$Z_i = \frac{V_i}{I_i}$$

Applying Kirchhoff's current law at node D we get,

$$I_i + I_d = g_m V_{gs} \qquad ...(10)$$

Looking at Fig. 10.35 we can write,

and 
$$V_{gs} = V_{i} \qquad ...(10.8)$$

$$V_{o} = -I_{d}(R_{D} || r_{d}) \qquad ...(10.8)$$

$$I_{d} = \frac{-V_{o}}{R_{D} || r_{d}} \qquad ...(10.8)$$

Substituting values of  $V_{gs}$  and  $I_{d}$  from equations 10.85 and 10.87 respectively equation 10.84 we get,

$$I_i - \frac{V_o}{R_D || r_d} = g_m V_i$$
...(10.8)

Applying KVL to the outer loop of Fig. 10.35 we get,
$$V_o = I_i (R_D || r_d) - g_m V_i (R_D || r_d) \qquad ... (10.8)$$
Substitute  $I_i = V_i - V_i$ 

$$I_{i} = \frac{V_{i} - V_{o}}{R_{F}} \dots (10^{90})$$

Substituting value of  $V_o$  from equation 10.89 in equation 10.90 we get,

$$I_{i} = \frac{V_{i} - (I_{i} - g_{m} V_{i})(R_{D} || r_{d})}{R_{F}}$$

$$I_{i+} \frac{I_{i}(R_{D} || r_{d})}{R_{F}} = \frac{V_{i} + g_{m} V_{i}(R_{D} || r_{d})}{R_{F}}$$

$$I_{i}(R_{F} + R_{D} || r_{d}) = \frac{V_{i}(1 + g_{m}(R_{D} || r_{d}))}{R_{F}}$$

E.D.

VGS

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